#### NPN 3.0A 60V Middle Power Transistor

Parameter	Value		
$V_{CEO}$	60		
I <sub>C</sub>	3A		

#### Features

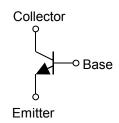
- 1) Suitable for Middle Power Driver
- 2) Complementary PNP Types: 2SA2071
- 3) Low  $V_{CE(sat)}$

 $V_{CE(sat)}$ =0.50V(Max.) ( $I_C/I_B$ =2A/200mA)

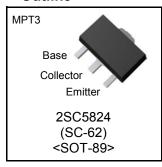
 $(I_C/I_B=2A/200MA)$ 

4) Lead Free/RoHS Compliant.

#### •Inner circuit



#### Outline



#### Applications

Motor driver , LED driver Power supply

#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SC5824	MPT3	4540	T100	180	12	1,000	UP

#### ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		$V_{CBO}$	60	V
Collector-emitter voltage		$V_{CEO}$	60	V
Emitter-base voltage	tter-base voltage V		6	V
Collector current	DC	I <sub>C</sub>	3.0	А
	Pulsed	I <sub>CP</sub> <sup>*1</sup>	6.0	А
Power dissipation		$P_{D}^{*2}$	0.5	W
		$P_{D}^{*3}$	2.0	W
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	−55 to +150	°C

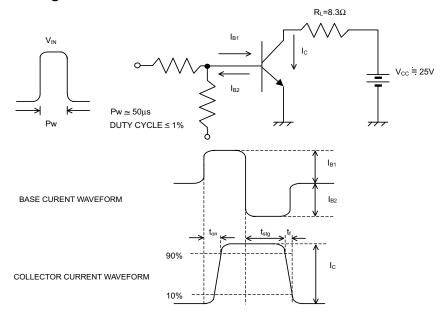
- \*1 Pw=100ms, single pulse
- \*2 Each terminal mounted on a reference land
- \*3 Mounted on a ceramic board (40×40×0.7 mm)

## ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	60	1	ı	V
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 100μA	60	ı	ı	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = 100μA	6	ı	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V	ı	ı	1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V	ı	ı	1	μА
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *1	$I_C = 2A, I_B = 200mA$	-	200	500	V
DC current gain	h <sub>FE</sub>	$V_{CE} = 2V, I_{C} = 100mA$	120	-	390	-
Transition frequency	f <sub>T</sub> *1	$V_{CE} = 10V, I_{E} = -100 \text{mA}$ f=10MH <sub>Z</sub>	ı	200	ı	MHz
Output capacitance	$C_{\sf ob}$	$V_{CB} = 10V$ , $I_E = 0A$ f = 1MHz	ı	20	ı	pF
Turn-on time	$t_{on}^{^{*2}}$	I <sub>C</sub> =3A	-	50	-	ns
Storage time	t <sub>stg</sub> *2	I <sub>B1</sub> =300mA I <sub>B2</sub> = -300mA	ı	150	-	ns
Fall time	t <sub>f</sub> *2	V <sub>CC</sub> ≃25V	-	30	-	ns

<sup>\*1</sup> Pulsed

# •Switching time test circuit



<sup>\*2</sup> See switching time test circuit

## ●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

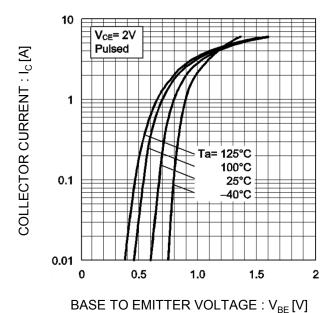
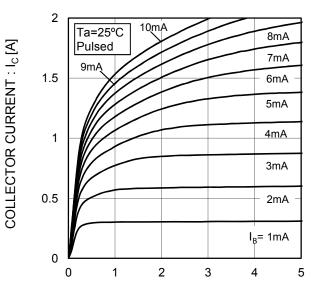


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE: V<sub>CE</sub>[V]

Fig.3 DC Current Gain vs. Collector Current(I)

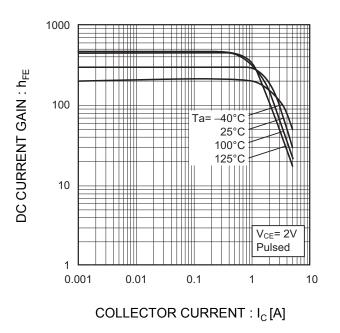
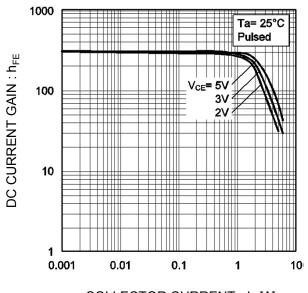
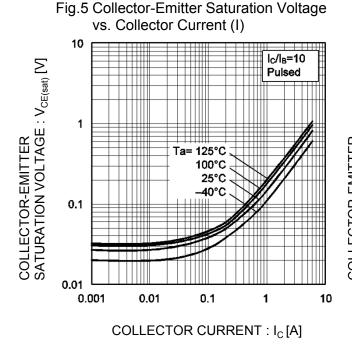


Fig.4 DC current Gain vs. Collector Current (II)



#### ●Electrical characteristic curves(Ta = 25°C)



VS. Collector Current (II)

10

Value (III)

Value (II

Fig.6 Collector-Emitter Saturation Voltage

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current 10 I<sub>C</sub>/I<sub>B</sub>=10/1 BASE-EMITTER SATURATION VOLTAGE : V<sub>BE(sat)</sub> [V] Pulsed Ta= -40°C 25°C 100°C 125°C 1 0.1 0.001 0.01 0.1 1 10 COLLECTOR CURRENT: Ic [A]

Fig.8 Gain Bandwidth Product
vs. Emitter Current

1000

100

100

Ta= 25°C

V<sub>CE</sub>= 10V

Pulsed

EMITTER CURRENT: I<sub>E</sub> [A]

## ●Electrical characteristic curves(Ta = 25°C)

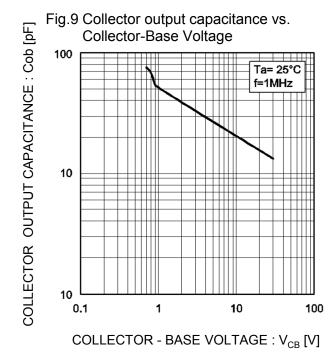
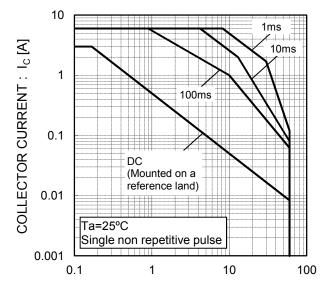
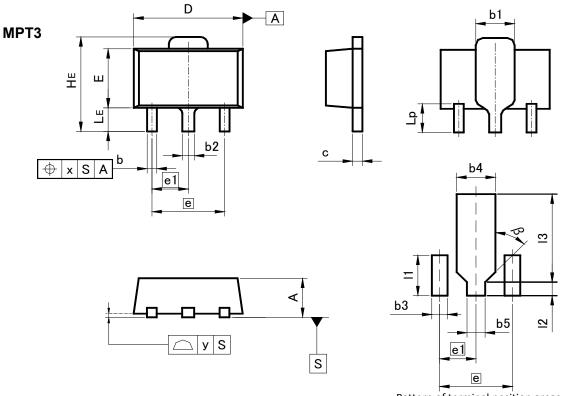


Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE :  $V_{CE}\left[V\right]$ 

## ●Dimensions (Unit : mm)



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.40	1.50	0.055	0.059	
b	0.30	0.50	0.012	0.020	
b1	1.50	1.70	0.059	0.067	
b2	0.40	0.60	0.016	0.024	
С	0.35	0.50	0.014	0.020	
D	4.40	4.70	0.173	0.185	
E	2.40	2.70	0.094	0.106	
е	3.00		0.118		
e1	1.50		0.059		
HE	3.70	4.30	0.146	0.169	
LE	0.80	1.20	0.031	0.047	
Lp	1.01	1.41	0.040	0.056	
X	_	0.15	ı	0.006	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
b3	-	0.65	1	0.026	
b4	-	1.70	ı	0.067	
b5	-	0.75	-	0.030	
l1	ı	1.71	ı	0.067	
12	ı	0.58	ı	0.023	
13	-	3.72	-	0.146	
β	45°		45°		

#### Dimension in mm / inches

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